

YO998426DIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Chan et al.

Serial No. 10/051,562

Group Art Unit: 2822

Filed: January 18, 2002

Examiner: Novacek, Christy L.

re: SELF-ALIGNED DOUBLE-GATE MOSFET BY SELECTIVE EPITAXY AND
SILICON WAFER BONDING TECHNIQUES

Commissioner For Patents
Alexandria, VA 22313-1450

AMENDMENT UNDER 37 C.F.R. §1.111

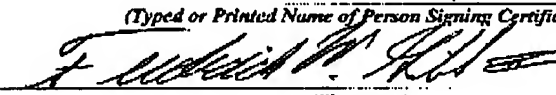
Sir:

In response to the Office Action mailed February 12, 2003, please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please cancel claim 24 without prejudice or disclaimer.

Please amend the remaining claims as follows:

CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)			Docket No. YO998-426DIV
Applicant(s): Chan et al.			
Serial No. 10/051,562	Filing Date January 18, 2002	Examiner C. Novacek	Group Art Unit 2822
Invention: SELF-ALIGNED DOUBLE GATE MOSFET BY SELECTIVE EPITAXY AND SILICON WAFER BONDING TECHNIQUES			
<p>I hereby certify that this <u>Amendment Under 37 CFR 1.111</u> (Identify type of correspondence)</p> <p>is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. 703-872-9318)</p> <p>on <u>May 9, 2003</u> (Date)</p> <p><u>Frederick W. Gibb, III</u> (Typed or Printed Name of Person Signing Certificate)</p> <p><u></u> (Signature)</p> <p>Note: Each paper must have its own certificate of mailing.</p> <p>FAX RECEIVED MAY 09 2003 TECHNOLOGY CENTER 2800</p>			